

CXTA42 NPN
CXTA92 PNP

SILICON COMPLIMENTARY
HIGH VOLTAGE TRANSISTOR



SOT-89 CASE

Central[™]
Semiconductor Corp.

DESCRIPTION:

The CENTRAL SEMICONDUCTOR CXTA42, CXTA92 types are complementary surface mount epoxy molded silicon planar epitaxial transistors designed for high voltage applications.

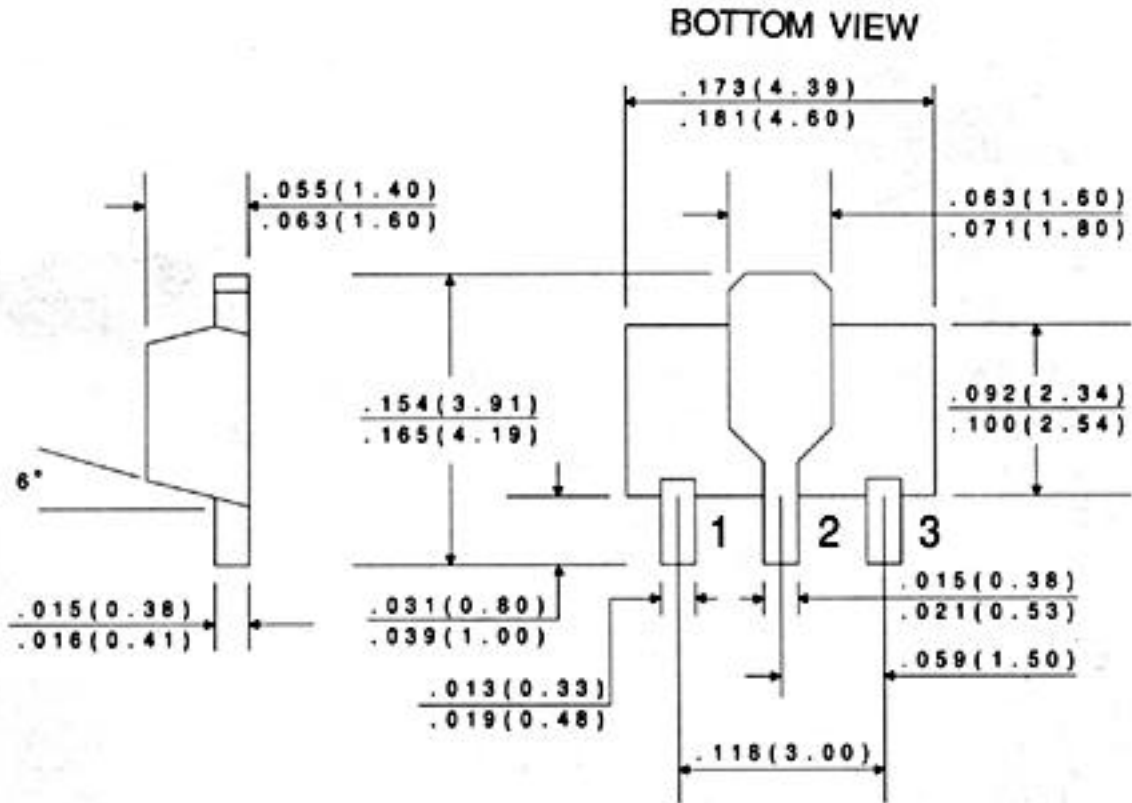
MAXIMUM RATINGS ($T_A=25^\circ\text{C}$)

	SYMBOL	CXTA42	CXTA92	UNITS
Collector-Base Voltage	V_{CBO}	300	300	V
Collector-Emitter Voltage	V_{CEO}	300	300	V
Emitter-Base Voltage	V_{EBO}	6.0	5.0	V
Collector Current	I_C		500	mA
Power Dissipation	P_D		1.2	W
Operating and Storage Junction Temperature	T_J, T_{stg}	-65 to +150		$^\circ\text{C}$
Thermal Resistance	θ_{JA}	104		$^\circ\text{C/W}$

ELECTRICAL CHARACTERISTICS ($T_A=25^\circ\text{C}$ unless otherwise noted)

SYMBOL	TEST CONDITIONS	CXTA42		CXTA92		UNITS
		MIN	MAX	MIN	MAX	
I_{CBO}	$V_{CB}=200\text{V}$		100		250	nA
I_{EBO}	$V_{BE}=6.0\text{V}$		100		-	nA
I_{EBO}	$V_{BE}=3.0\text{V}$		-		100	nA
BV_{CBO}	$I_C=100\mu\text{A}$	300		300		V
BV_{CEO}	$I_C=1.0\text{mA}$	300		300		V
BV_{EBO}	$I_E=100\mu\text{A}$	6.0		5.0		V
$V_{CE(SAT)}$	$I_C=20\text{mA}, I_B=2.0\text{mA}$		0.5		0.5	V
$V_{BE(SAT)}$	$I_C=20\text{mA}, I_B=2.0\text{mA}$		0.9		0.9	V
h_{FE}	$V_{CE}=10\text{V}, I_C=1.0\text{mA}$	25		25		
h_{FE}	$V_{CE}=10\text{V}, I_C=10\text{mA}$	40		40		
h_{FE}	$V_{CE}=10\text{V}, I_C=30\text{mA}$	40		25		
f_T	$V_{CE}=20\text{V}, I_C=10\text{mA}, f=100\text{MHz}$	50		50		MHz
C_{ob}	$V_{CB}=20\text{V}, I_E=0, f=1.0\text{MHz}$		3.0		6.0	pF

All dimensions in inches (mm).



LEAD CODE:

- 1) EMITTER
- 2) COLLECTOR
- 3) BASE